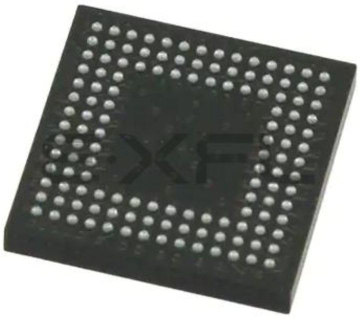
Lattice Semiconductor Corporation - LFXP2-8E-5MN132C Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	1000
Number of Logic Elements/Cells	8000
Total RAM Bits	226304
Number of I/O	86
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	132-LFBGA, CSPBGA
Supplier Device Package	132-CSBGA (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfxp2-8e-5mn132c

Email: info@E-XFL.COM

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LatticeXP2 Family Data Sheet Introduction

February 2012 Data Sheet DS1009

Features

- **flexiFLASH™ Architecture**
  - Instant-on
  - Infinitely reconfigurable
  - Single chip
  - FlashBAK™ technology
  - Serial TAG memory
  - Design security
- **Live Update Technology**
  - TransFR™ technology
  - Secure updates with 128 bit AES encryption
  - Dual-boot with external SPI
- **sysDSP™ Block**
  - Three to eight blocks for high performance Multiply and Accumulate
  - 12 to 32 18x18 multipliers
  - Each block supports one 36x36 multiplier or four 18x18 or eight 9x9 multipliers
- **Embedded and Distributed Memory**
  - Up to 885 Kbits sysMEM™ EBR
  - Up to 83 Kbits Distributed RAM
- **sysCLOCK™ PLLs**
  - Up to four analog PLLs per device
  - Clock multiply, divide and phase shifting
- **Flexible I/O Buffer**
  - sysIO™ buffer supports:
    - LVCMOS 33/25/18/15/12; LVTTL
    - SSTL 33/25/18 class I, II
    - HSTL15 class I; HSTL18 class I, II
    - PCI
    - LVDS, Bus-LVDS, MLVDS, LVPECL, RSDS
- **Pre-engineered Source Synchronous Interfaces**
  - DDR / DDR2 interfaces up to 200 MHz
  - 7:1 LVDS interfaces support display applications
  - XGMII
- **Density And Package Options**
  - 5k to 40k LUT4s, 86 to 540 I/Os
  - csBGA, TQFP, PQFP, ftBGA and fpBGA packages
  - Density migration supported
- **Flexible Device Configuration**
  - SPI (master and slave) Boot Flash Interface
  - Dual Boot Image supported
  - Soft Error Detect (SED) macro embedded
- **System Level Support**
  - IEEE 1149.1 and IEEE 1532 Compliant
  - On-chip oscillator for initialization & general use
  - Devices operate with 1.2V power supply

Table 1-1. LatticeXP2 Family Selection Guide

Device	XP2-5	XP2-8	XP2-17	XP2-30	XP2-40
LUTs (K)	5	8	17	29	40
Distributed RAM (KBits)	10	18	35	56	83
EBR SRAM (KBits)	166	221	276	387	885
EBR SRAM Blocks	9	12	15	21	48
sysDSP Blocks	3	4	5	7	8
18 x 18 Multipliers	12	16	20	28	32
V_{CC} Voltage	1.2	1.2	1.2	1.2	1.2
GPLL	2	2	4	4	4
Max Available I/O	172	201	358	472	540
Packages and I/O Combinations					
132-Ball csBGA (8 x 8 mm)	86	86			
144-Pin TQFP (20 x 20 mm)	100	100			
208-Pin PQFP (28 x 28 mm)	146	146	146		
256-Ball ftBGA (17 x17 mm)	172	201	201	201	
484-Ball fpBGA (23 x 23 mm)			358	363	363
672-Ball fpBGA (27 x 27 mm)				472	540

Modes of Operation

Each slice has up to four potential modes of operation: Logic, Ripple, RAM and ROM.

Logic Mode

In this mode, the LUTs in each slice are configured as LUT4s. A LUT4 has 16 possible input combinations. Four-input logic functions are generated by programming the LUT4. Since there are two LUT4s per slice, a LUT5 can be constructed within one slice. Larger LUTs such as LUT6, LUT7 and LUT8, can be constructed by concatenating two or more slices. Note that a LUT8 requires more than four slices.

Ripple Mode

Ripple mode allows efficient implementation of small arithmetic functions. In ripple mode, the following functions can be implemented by each slice:

- Addition 2-bit
- Subtraction 2-bit
- Add/Subtract 2-bit using dynamic control
- Up counter 2-bit
- Down counter 2-bit
- Up/Down counter with async clear
- Up/Down counter with preload (sync)
- Ripple mode multiplier building block
- Multiplier support
- Comparator functions of A and B inputs
    - A greater-than-or-equal-to B
    - A not-equal-to B
    - A less-than-or-equal-to B

Two carry signals, FCI and FCO, are generated per slice in this mode, allowing fast arithmetic functions to be constructed by concatenating slices.

RAM Mode

In this mode, a 16x4-bit distributed Single Port RAM (SPR) can be constructed using each LUT block in Slice 0 and Slice 2 as a 16x1-bit memory. Slice 1 is used to provide memory address and control signals. A 16x2-bit Pseudo Dual Port RAM (PDPR) memory is created by using one slice as the read-write port and the other companion slice as the read-only port.

The Lattice design tools support the creation of a variety of different size memories. Where appropriate, the software will construct these using distributed memory primitives that represent the capabilities of the PFU. Table 2-3 shows the number of slices required to implement different distributed RAM primitives. For more information on using RAM in LatticeXP2 devices, please see TN1137, LatticeXP2 Memory Usage Guide.

Table 2-3. Number of Slices Required For Implementing Distributed RAM

	SPR 16X4	PDPR 16X4
Number of slices	3	3

Note: SPR = Single Port RAM, PDPR = Pseudo Dual Port RAM

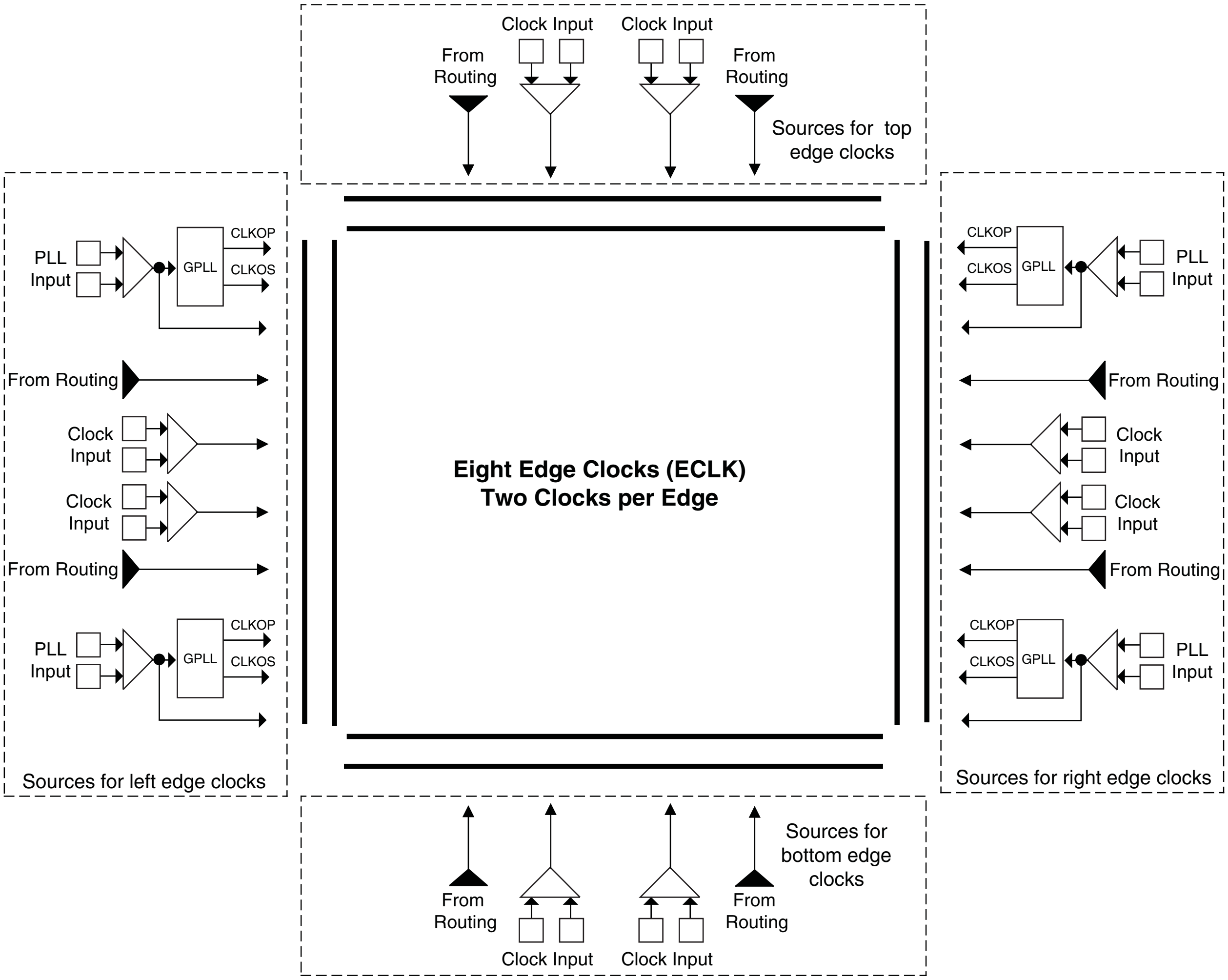
ROM Mode

ROM mode uses the LUT logic; hence, Slices 0 through 3 can be used in the ROM mode. Preloading is accomplished through the programming interface during PFU configuration.

Edge Clock Sources

Edge clock resources can be driven from a variety of sources at the same edge. Edge clock resources can be driven from adjacent edge clock PIOs, primary clock PIOs, PLLs and clock dividers as shown in Figure 2-8.

Figure 2-8. Edge Clock Sources

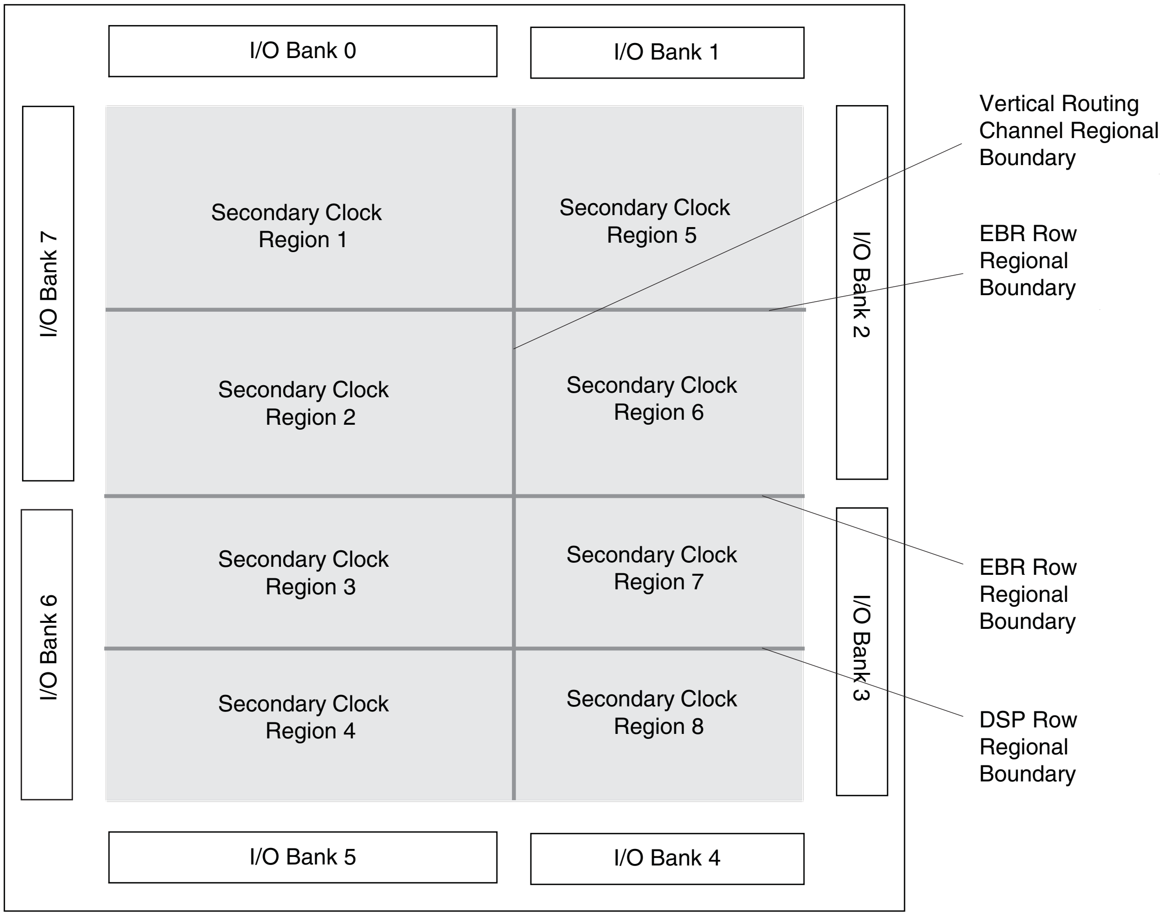


Note: This diagram shows sources for the XP2-17 device. Smaller LatticeXP2 devices have two GPLLs.

LatticeXP2-30 and smaller devices have six secondary clock regions. All devices in the LatticeXP2 family have four secondary clocks (SC0 to SC3) which are distributed to every region.

The secondary clock muxes are located in the center of the device. Figure 2-12 shows the mux structure of the secondary clock routing. Secondary clocks SC0 to SC3 are used for clock and control and SC4 to SC7 are used for high fan-out signals.

Figure 2-11. Secondary Clock Regions XP2-40



sysMEM Memory

LatticeXP2 devices contains a number of sysMEM Embedded Block RAM (EBR). The EBR consists of 18 Kbit RAM with dedicated input and output registers.

sysMEM Memory Block

The sysMEM block can implement single port, dual port or pseudo dual port memories. Each block can be used in a variety of depths and widths as shown in Table 2-5. FIFOs can be implemented in sysMEM EBR blocks by using support logic with PFUs. The EBR block supports an optional parity bit for each data byte to facilitate parity checking. EBR blocks provide byte-enable support for configurations with18-bit and 36-bit data widths.

Table 2-5. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36
True Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18
Pseudo Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36

Bus Size Matching

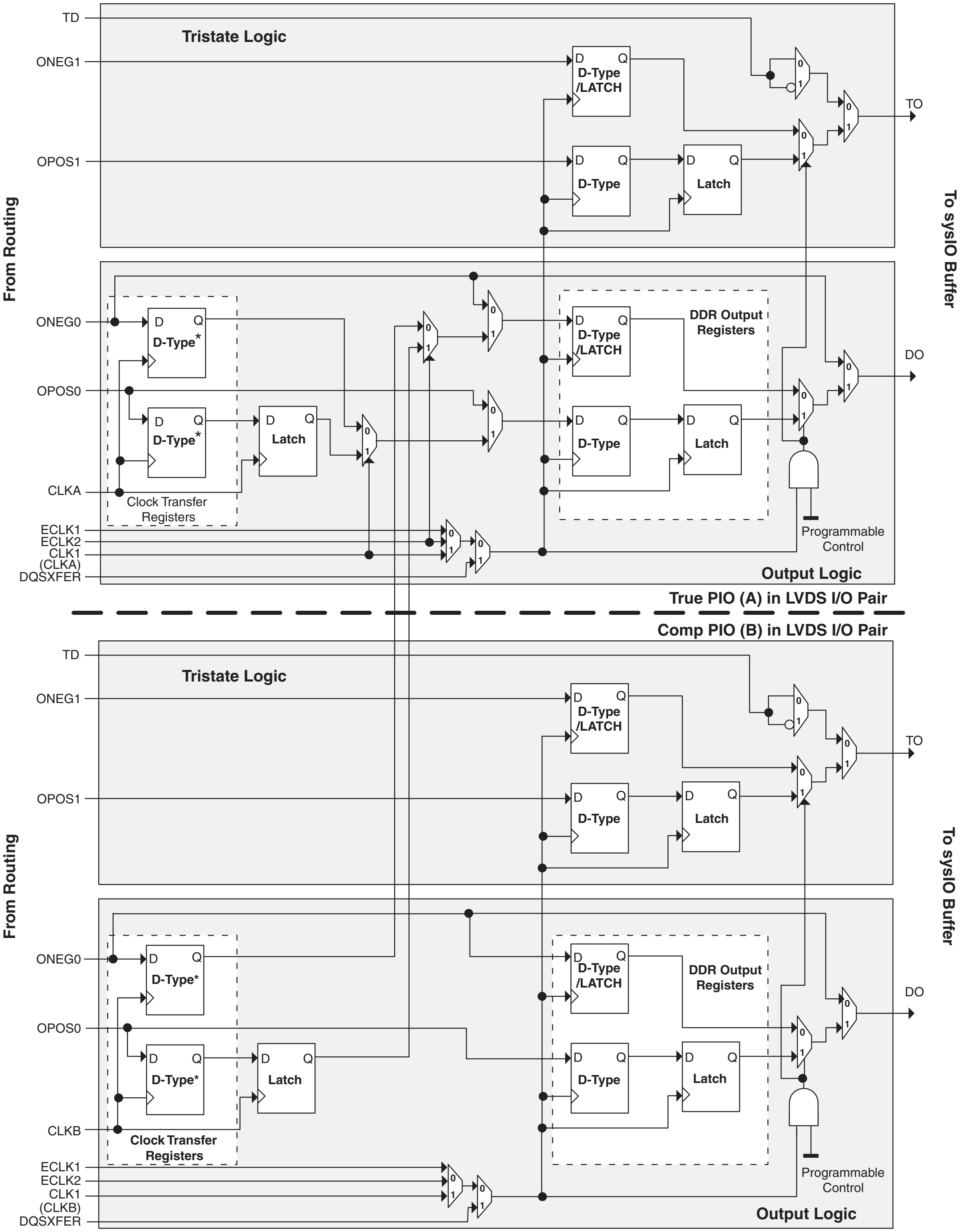
All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

FlashBAK EBR Content Storage

All the EBR memory in the LatticeXP2 is shadowed by Flash memory. Optionally, initialization values for the memory blocks can be defined using the Lattice Diamond design tools. The initialization values are loaded into the Flash memory during device programming and into the SRAM at power up or whenever the device is reconfigured. This feature is ideal for the storage of a variety of information such as look-up tables and microprocessor code. It is also possible to write the current contents of the EBR memory back to Flash memory. This capability is useful for the storage of data such as error codes and calibration information. For additional information on the FlashBAK capability see TN1137, LatticeXP2 Memory Usage Guide.

shows the diagram using this gearbox function. For more information on this topic, see TN1138, LatticeXP2 High Speed I/O Interface.

Figure 2-27. Output and Tristate Block



* Shared with input register

Note: Simplified version does not show CE and SET/RESET details

Figure 2-28. DQS Input Routing (Left and Right)

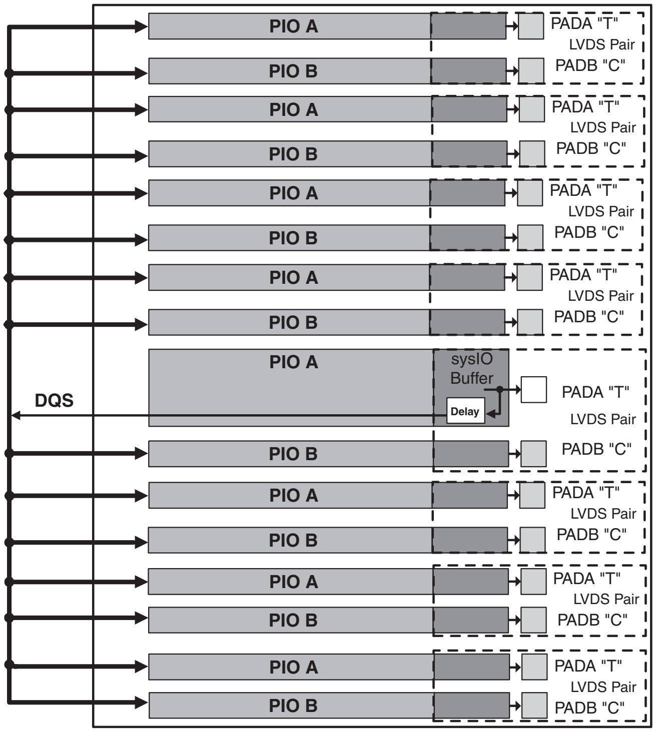
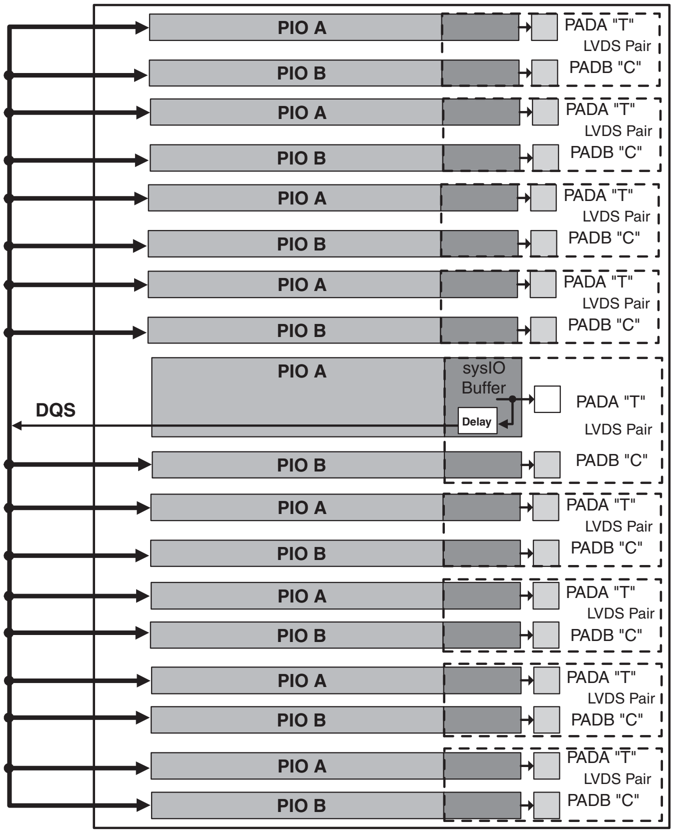


Figure 2-29. DQS Input Routing (Top and Bottom)



DQSXFER

LatticeXP2 devices provide a DQSXFER signal to the output buffer to assist it in data transfer to DDR memories that require DQS strobe be shifted 90°. This shifted DQS strobe is generated by the DQSDEL block. The DQSXFER signal runs the span of the data bus.

sysIO Buffer

Each I/O is associated with a flexible buffer referred to as a sysIO buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysIO buffers allow users to implement the wide variety of standards that are found in today's systems including LVCMOS, SSTL, HSTL, LVDS and LVPECL.

sysIO Buffer Banks

LatticeXP2 devices have eight sysIO buffer banks for user I/Os arranged two per side. Each bank is capable of supporting multiple I/O standards. Each sysIO bank has its own I/O supply voltage (V_{CCIO}). In addition, each bank has voltage references, V_{REF1} and V_{REF2}, that allow it to be completely independent from the others. Figure 2-32 shows the eight banks and their associated supplies.

In LatticeXP2 devices, single-ended output buffers and ratioed input buffers (LVTTL, LVCMOS and PCI) are powered using V_{CCIO}. LVTTL, LVCMOS33, LVCMOS25 and LVCMOS12 can also be set as fixed threshold inputs independent of V_{CCIO}.

Each bank can support up to two separate V_{REF} voltages, V_{REF1} and V_{REF2}, that set the threshold for the referenced input buffers. Some dedicated I/O pins in a bank can be configured to be a reference voltage supply pin. Each I/O is individually configurable based on the bank's supply and reference voltages.

Figure 2-32. LatticeXP2 Banks

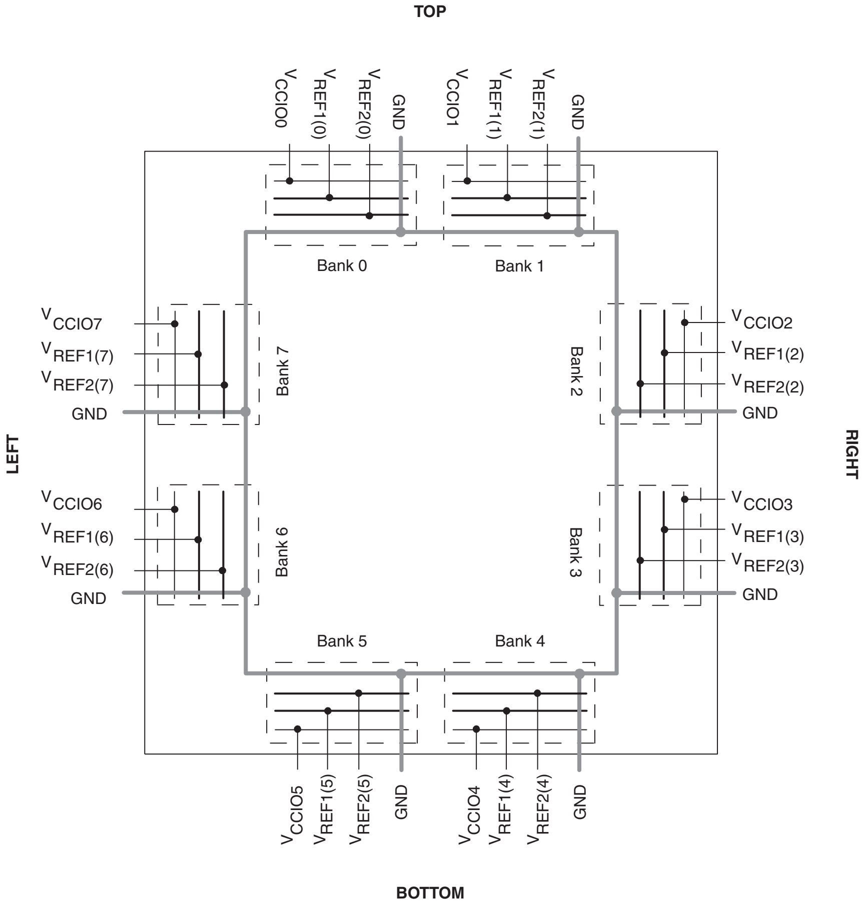


Table 2-13. Supported Output Standards

Output Standard	Drive	V_{CCIO} (Nom.)
Single-ended Interfaces		
LVTTL	4mA, 8mA, 12mA, 16mA, 20mA	3.3
LVCMOS33	4mA, 8mA, 12mA 16mA, 20mA	3.3
LVCMOS25	4mA, 8mA, 12mA, 16mA, 20mA	2.5
LVCMOS18	4mA, 8mA, 12mA, 16mA	1.8
LVCMOS15	4mA, 8mA	1.5
LVCMOS12	2mA, 6mA	1.2
LVCMOS33, Open Drain	4mA, 8mA, 12mA 16mA, 20mA	—
LVCMOS25, Open Drain	4mA, 8mA, 12mA 16mA, 20mA	—
LVCMOS18, Open Drain	4mA, 8mA, 12mA 16mA	—
LVCMOS15, Open Drain	4mA, 8mA	—
LVCMOS12, Open Drain	2mA, 6mA	—
PCI33	N/A	3.3
HSTL18 Class I, II	N/A	1.8
HSTL15 Class I	N/A	1.5
SSTL33 Class I, II	N/A	3.3
SSTL25 Class I, II	N/A	2.5
SSTL18 Class I, II	N/A	1.8
Differential Interfaces		
Differential SSTL33, Class I, II	N/A	3.3
Differential SSTL25, Class I, II	N/A	2.5
Differential SSTL18, Class I, II	N/A	1.8
Differential HSTL18, Class I, II	N/A	1.8
Differential HSTL15, Class I	N/A	1.5
LVDS[1, 2]	N/A	2.5
MLVDS[1]	N/A	2.5
BLVDS[1]	N/A	2.5
LVPECL[1]	N/A	3.3
RSDS[1]	N/A	2.5
LVCMOS33D[1]	4mA, 8mA, 12mA, 16mA, 20mA	3.3

1. Emulated with external resistors.
2. On the left and right edges, LVDS outputs are supported with a dedicated differential output driver on 50% of the I/Os. This solution does not require external resistors at the driver.

Hot Socketing

LatticeXP2 devices have been carefully designed to ensure predictable behavior during power-up and power-down. Power supplies can be sequenced in any order. During power-up and power-down sequences, the I/Os remain in tri-state until the power supply voltage is high enough to ensure reliable operation. In addition, leakage into I/O pins is controlled to within specified limits. This allows for easy integration with the rest of the system. These capabilities make the LatticeXP2 ideal for many multiple power supply and hot-swap applications.

IEEE 1149.1-Compliant Boundary Scan Testability

All LatticeXP2 devices have boundary scan cells that are accessed through an IEEE 1149.1 compliant Test Access Port (TAP). This allows functional testing of the circuit board, on which the device is mounted, through a serial scan path that can access all critical logic nodes. Internal registers are linked internally, allowing test data to be shifted in original backup configuration and try again. This all can be done without power cycling the system. For more information please see TN1220, LatticeXP2 Dual Boot Feature.

For more information on device configuration, please see TN1141, LatticeXP2 sysCONFIG Usage Guide.

Soft Error Detect (SED) Support

LatticeXP2 devices have dedicated logic to perform Cyclic Redundancy Code (CRC) checks. During configuration, the configuration data bitstream can be checked with the CRC logic block. In addition, LatticeXP2 devices can be programmed for checking soft errors in SRAM. SED can be run on a programmed device when the user logic is not active. In the event a soft error occurs, the device can be programmed to either reload from a known good boot image (from internal Flash or external SPI memory) or generate an error signal.

For further information on SED support, please see TN1130, LatticeXP2 Soft Error Detection (SED) Usage Guide.

On-Chip Oscillator

Every LatticeXP2 device has an internal CMOS oscillator that is used to derive a Master Clock (CCLK) for configuration. The oscillator and CCLK run continuously and are available to user logic after configuration is complete. The available CCLK frequencies are listed in Table 2-14. When a different CCLK frequency is selected during the design process, the following sequence takes place:

1. Device powers up with the default CCLK frequency.
2. During configuration, users select a different CCLK frequency.
3. CCLK frequency changes to the selected frequency after clock configuration bits are received.

This internal CMOS oscillator is available to the user by routing it as an input clock to the clock tree. For further information on the use of this oscillator for configuration or user mode, please see TN1141, LatticeXP2 sysCONFIG Usage Guide.

Table 2-14. Selectable CCLKs and Oscillator Frequencies During Configuration and User Mode

CCLK/Oscillator (MHz)
2.5[1]
3.1[2]
4.3
5.4
6.9
8.1
9.2
10
13
15
20
26
32
40
54
80[3]
163[3]

1. Software default oscillator frequency.
2. Software default CCLK frequency.
3. Frequency not valid for CCLK.

LatticeXP2 Family Data Sheet
DC and Switching Characteristics

September 2014 **Data Sheet DS1009**

Absolute Maximum Ratings[1, 2, 3]

Supply Voltage V_{CC}	-0.5 to 1.32V
Supply Voltage V_{CCAUX}	-0.5 to 3.75V
Supply Voltage V_{CCJ}	-0.5 to 3.75V
Supply Voltage V_{CCPLL}[4]	-0.5 to 3.75V
Output Supply Voltage V_{CCIO}	-0.5 to 3.75V
Input or I/O Tristate Voltage Applied[5]	-0.5 to 3.75V
Storage Temperature (Ambient)	-65 to 150°C
Junction Temperature Under Bias (Tj)	+125°C

1. Stress above those listed under the “Absolute Maximum Ratings” may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.
2. Compliance with the Lattice Thermal Management document is required.
3. All voltages referenced to GND.
4. V_{CCPLL} only available on csBGA, PQFP and TQFP packages.
5. Overshoot and undershoot of -2V to (V_{IHMAX} + 2) volts is permitted for a duration of <20 ns.

Recommended Operating Conditions

Symbol	Parameter	Min.	Max.	Units
V_{CC}	Core Supply Voltage	1.14	1.26	V
V_{CCAUX}[4, 5]	Auxiliary Supply Voltage	3.135	3.465	V
V_{CCPLL}[1]	PLL Supply Voltage	3.135	3.465	V
V_{CCIO}[2, 3, 4]	I/O Driver Supply Voltage	1.14	3.465	V
V_{CCJ}[2]	Supply Voltage for IEEE 1149.1 Test Access Port	1.14	3.465	V
t_{JCOM}	Junction Temperature, Commercial Operation	0	85	°C
t_{JIND}	Junction Temperature, Industrial Operation	-40	100	°C

1. V_{CCPLL} only available on csBGA, PQFP and TQFP packages.
2. If V_{CCIO} or V_{CCJ} is set to 1.2 V, they must be connected to the same power supply as V_{CC}. If V_{CCIO} or V_{CCJ} is set to 3.3V, they must be connected to the same power supply as V_{CCAUX}.
3. See recommended voltages by I/O standard in subsequent table.
4. To ensure proper I/O behavior, V_{CCIO} must be turned off at the same time or earlier than V_{CCAUX}.
5. In fpBGA and ftBGA packages, the PLLs are connected to, and powered from, the auxiliary power supply.

On-Chip Flash Memory Specifications

Symbol	Parameter	Max.	Units
$N_{PROGCYC}$	Flash Programming Cycles per $t_{RETENTION}$[1]	10,000	Cycles
	Flash Functional Programming Cycles	100,000	

1. The minimum data retention, $t_{RETENTION}$, is 20 years.

sysIO Recommended Operating Conditions

Over Recommended Operating Conditions

Standard	V_{CCIO}			V_{REF} (V)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
LVCMOS33[2]	3.135	3.3	3.465	—	—	—
LVCMOS25[2]	2.375	2.5	2.625	—	—	—
LVCMOS18	1.71	1.8	1.89	—	—	—
LVCMOS15	1.425	1.5	1.575	—	—	—
LVCMOS12[2]	1.14	1.2	1.26	—	—	—
LVTTL33[2]	3.135	3.3	3.465	—	—	—
PCI33	3.135	3.3	3.465	—	—	—
SSTL18_I[2], SSTL18_II[2]	1.71	1.8	1.89	0.833	0.9	0.969
SSTL25_I[2], SSTL25_II[2]	2.375	2.5	2.625	1.15	1.25	1.35
SSTL33_I[2], SSTL33_II[2]	3.135	3.3	3.465	1.3	1.5	1.7
HSTL15_I[2]	1.425	1.5	1.575	0.68	0.75	0.9
HSTL18_I[2], HSTL18_II[2]	1.71	1.8	1.89	0.816	0.9	1.08
LVDS25[2]	2.375	2.5	2.625	—	—	—
MLVDS25[1]	2.375	2.5	2.625	—	—	—
LVPECL33[1, 2]	3.135	3.3	3.465	—	—	—
BLVDS25[1, 2]	2.375	2.5	2.625	—	—	—
RSDS[1, 2]	2.375	2.5	2.625	—	—	—
SSTL18D_I[2], SSTL18D_II[2]	1.71	1.8	1.89	—	—	—
SSTL25D_ I[2], SSTL25D_II[2]	2.375	2.5	2.625	—	—	—
SSTL33D_ I[2], SSTL33D_ II[2]	3.135	3.3	3.465	—	—	—
HSTL15D_ I[2]	1.425	1.5	1.575	—	—	—
HSTL18D_ I[2], HSTL18D_ II[2]	1.71	1.8	1.89	—	—	—

1. Inputs on chip. Outputs are implemented with the addition of external resistors.
2. Input on this standard does not depend on the value of V_{CCIO}.

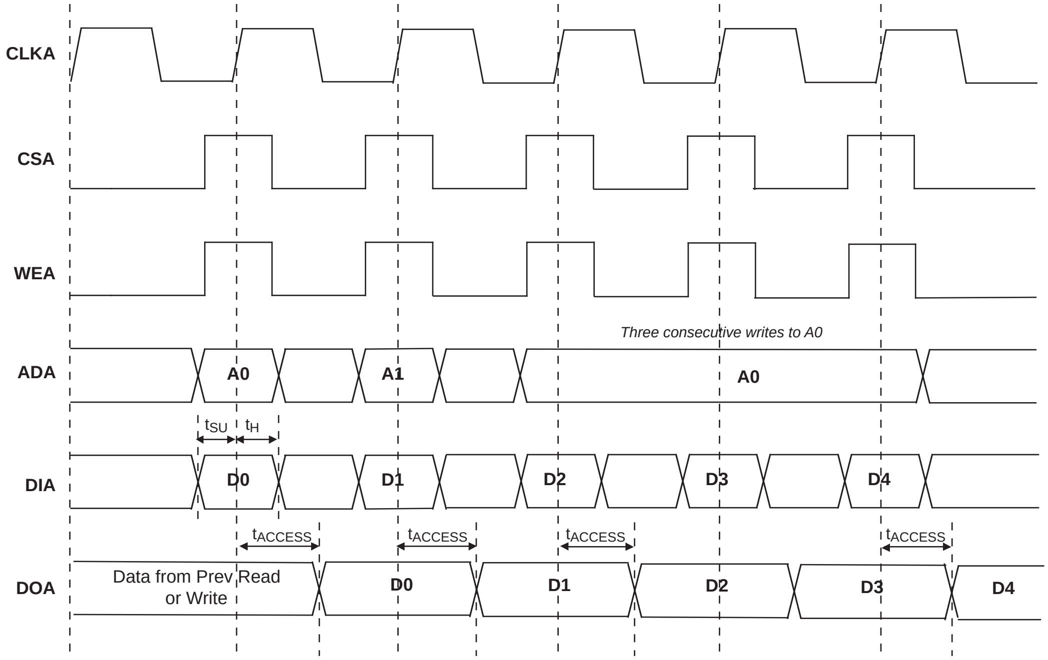
LatticeXP2 Internal Switching Characteristics[1] (Continued)

Over Recommended Operating Conditions

Parameter	Description	-7		-6		-5		Units
		Min.	Max.	Min.	Max.	Min.	Max.	
t_{HP_DSP}	Pipeline Register Hold Time	-0.787	—	-0.890	—	-0.994	—	ns
t_{SUO_DSP}	Output Register Setup Time	4.896	—	5.413	—	5.931	—	ns
t_{HO_DSP}	Output Register Hold Time	-1.439	—	-1.604	—	-1.770	—	ns
t_{COI_DSP}[3]	Input Register Clock to Output Time	—	4.513	—	4.947	—	5.382	ns
t_{COP_DSP}[3]	Pipeline Register Clock to Output Time	—	2.153	—	2.272	—	2.391	ns
t_{COO_DSP}[3]	Output Register Clock to Output Time	—	0.569	—	0.600	—	0.631	ns
$t_{SUADSUB}$	AdSub Input Register Setup Time	-0.270	—	-0.298	—	-0.327	—	ns
t_{HADSUB}	AdSub Input Register Hold Time	0.306	—	0.338	—	0.371	—	ns

1. Internal parameters are characterized, but not tested on every device.
2. RST resets VCO and all counters in PLL.
3. These parameters include the Adder Subtractor block in the path.

Figure 3-8. Write Through (SP Read/Write on Port A, Input Registers Only)



Note: Input data and address are registered at the positive edge of the clock and output data appears after the positive edge of the clock.

LatticeXP2 Family Timing Adders[1, 2, 3, 4] (Continued)

Over Recommended Operating Conditions

Buffer Type	Description	-7	-6	-5	Units
HSTL15_I	HSTL_15 class I 4mA drive	0.32	0.69	1.06	ns
HSTL15D_I	Differential HSTL 15 class I 4mA drive	0.32	0.69	1.06	ns
SSTL33_I	SSTL_3 class I	-0.25	0.05	0.35	ns
SSTL33_II	SSTL_3 class II	-0.31	-0.02	0.27	ns
SSTL33D_I	Differential SSTL_3 class I	-0.25	0.05	0.35	ns
SSTL33D_II	Differential SSTL_3 class II	-0.31	-0.02	0.27	ns
SSTL25_I	SSTL_2 class I 8mA drive	-0.25	0.02	0.30	ns
SSTL25_II	SSTL_2 class II 16mA drive	-0.28	0.00	0.28	ns
SSTL25D_I	Differential SSTL_2 class I 8mA drive	-0.25	0.02	0.30	ns
SSTL25D_II	Differential SSTL_2 class II 16mA drive	-0.28	0.00	0.28	ns
SSTL18_I	SSTL_1.8 class I	-0.17	0.13	0.43	ns
SSTL18_II	SSTL_1.8 class II 8mA drive	-0.18	0.12	0.42	ns
SSTL18D_I	Differential SSTL_1.8 class I	-0.17	0.13	0.43	ns
SSTL18D_II	Differential SSTL_1.8 class II 8mA drive	-0.18	0.12	0.42	ns
LVTTL33_4mA	LVTTL 4mA drive	-0.37	-0.05	0.26	ns
LVTTL33_8mA	LVTTL 8mA drive	-0.45	-0.18	0.10	ns
LVTTL33_12mA	LVTTL 12mA drive	-0.52	-0.24	0.04	ns
LVTTL33_16mA	LVTTL 16mA drive	-0.43	-0.14	0.14	ns
LVTTL33_20mA	LVTTL 20mA drive	-0.46	-0.18	0.09	ns
LVCMOS33_4mA	LVCMOS 3.3 4mA drive, fast slew rate	-0.37	-0.05	0.26	ns
LVCMOS33_8mA	LVCMOS 3.3 8mA drive, fast slew rate	-0.45	-0.18	0.10	ns
LVCMOS33_12mA	LVCMOS 3.3 12mA drive, fast slew rate	-0.52	-0.24	0.04	ns
LVCMOS33_16mA	LVCMOS 3.3 16mA drive, fast slew rate	-0.43	-0.14	0.14	ns
LVCMOS33_20mA	LVCMOS 3.3 20mA drive, fast slew rate	-0.46	-0.18	0.09	ns
LVCMOS25_4mA	LVCMOS 2.5 4mA drive, fast slew rate	-0.42	-0.15	0.13	ns
LVCMOS25_8mA	LVCMOS 2.5 8mA drive, fast slew rate	-0.48	-0.21	0.05	ns
LVCMOS25_12mA	LVCMOS 2.5 12mA drive, fast slew rate	0.00	0.00	0.00	ns
LVCMOS25_16mA	LVCMOS 2.5 16mA drive, fast slew rate	-0.45	-0.18	0.08	ns
LVCMOS25_20mA	LVCMOS 2.5 20mA drive, fast slew rate	-0.49	-0.22	0.04	ns
LVCMOS18_4mA	LVCMOS 1.8 4mA drive, fast slew rate	-0.46	-0.18	0.10	ns
LVCMOS18_8mA	LVCMOS 1.8 8mA drive, fast slew rate	-0.52	-0.25	0.02	ns
LVCMOS18_12mA	LVCMOS 1.8 12mA drive, fast slew rate	-0.56	-0.30	-0.03	ns
LVCMOS18_16mA	LVCMOS 1.8 16mA drive, fast slew rate	-0.50	-0.24	0.03	ns
LVCMOS15_4mA	LVCMOS 1.5 4mA drive, fast slew rate	-0.45	-0.17	0.11	ns
LVCMOS15_8mA	LVCMOS 1.5 8mA drive, fast slew rate	-0.53	-0.26	0.00	ns
LVCMOS12_2mA	LVCMOS 1.2 2mA drive, fast slew rate	-0.46	-0.19	0.08	ns
LVCMOS12_6mA	LVCMOS 1.2 6mA drive, fast slew rate	-0.55	-0.29	-0.02	ns
LVCMOS33_4mA	LVCMOS 3.3 4mA drive, slow slew rate	0.98	1.41	1.84	ns
LVCMOS33_8mA	LVCMOS 3.3 8mA drive, slow slew rate	0.74	1.16	1.58	ns
LVCMOS33_12mA	LVCMOS 3.3 12mA drive, slow slew rate	0.56	0.97	1.38	ns
LVCMOS33_16mA	LVCMOS 3.3 16mA drive, slow slew rate	0.77	1.19	1.61	ns
LVCMOS33_20mA	LVCMOS 3.3 20mA drive, slow slew rate	0.57	0.98	1.40	ns

LatticeXP2 Family Timing Adders[1, 2, 3, 4] (Continued)

Over Recommended Operating Conditions

Buffer Type	Description	-7	-6	-5	Units
LVCMOS25_4mA	LVCMOS 2.5 4mA drive, slow slew rate	1.05	1.43	1.81	ns
LVCMOS25_8mA	LVCMOS 2.5 8mA drive, slow slew rate	0.78	1.15	1.52	ns
LVCMOS25_12mA	LVCMOS 2.5 12mA drive, slow slew rate	0.59	0.96	1.33	ns
LVCMOS25_16mA	LVCMOS 2.5 16mA drive, slow slew rate	0.81	1.18	1.55	ns
LVCMOS25_20mA	LVCMOS 2.5 20mA drive, slow slew rate	0.61	0.98	1.35	ns
LVCMOS18_4mA	LVCMOS 1.8 4mA drive, slow slew rate	1.01	1.38	1.75	ns
LVCMOS18_8mA	LVCMOS 1.8 8mA drive, slow slew rate	0.72	1.08	1.45	ns
LVCMOS18_12mA	LVCMOS 1.8 12mA drive, slow slew rate	0.53	0.90	1.26	ns
LVCMOS18_16mA	LVCMOS 1.8 16mA drive, slow slew rate	0.74	1.11	1.48	ns
LVCMOS15_4mA	LVCMOS 1.5 4mA drive, slow slew rate	0.96	1.33	1.71	ns
LVCMOS15_8mA	LVCMOS 1.5 8mA drive, slow slew rate	-0.53	-0.26	0.00	ns
LVCMOS12_2mA	LVCMOS 1.2 2mA drive, slow slew rate	0.90	1.27	1.65	ns
LVCMOS12_6mA	LVCMOS 1.2 6mA drive, slow slew rate	-0.55	-0.29	-0.02	ns
PCI33	3.3V PCI	-0.29	-0.01	0.26	ns

1. Timing Adders are characterized but not tested on every device.
2. LVCMOS timing measured with the load specified in Switching Test Condition table.
3. All other standards tested according to the appropriate specifications.
4. The base parameters used with these timing adders to calculate timing are listed in the LatticeXP2 Internal Switching Characteristics table under PIO Input/Output Timing.
5. These timing adders are measured with the recommended resistor values.

LatticeXP2 sysCONFIG Port Timing Specifications

Over Recommended Operating Conditions

Parameter	Description	Min	Max	Units
sysCONFIG POR, Initialization and Wake Up				
t_{ICFG}	Minimum Vcc to INITN High	—	50	ms
t_{VMC}	Time from t_{ICFG} to valid Master CCLK	—	2	µs
t_{PRGMRJ}	PROGRAMN Pin Pulse Rejection	—	12	ns
t_{PRGM}	PROGRAMN Low Time to Start Configuration	50	—	ns
t_{DINIT}[1]	PROGRAMN High to INITN High Delay	—	1	ms
$t_{DPPINIT}$	Delay Time from PROGRAMN Low to INITN Low	—	50	ns
$t_{DPPDONE}$	Delay Time from PROGRAMN Low to DONE Low	—	50	ns
t_{IODISS}	User I/O Disable from PROGRAMN Low	—	35	ns
t_{IOENSS}	User I/O Enabled Time from CCLK Edge During Wake-up Sequence	—	25	ns
t_{MWC}	Additional Wake Master Clock Signals after DONE Pin High	0	—	Cycles
sysCONFIG SPI Port (Master)				
t_{CFGX}	INITN High to CCLK Low	—	1	µs
t_{CSSPI}	INITN High to CSSPIN Low	—	2	µs
t_{CSCCLK}	CCLK Low before CSSPIN Low	0	—	ns
t_{SOCDO}	CCLK Low to Output Valid	—	15	ns
t_{CSPID}	CSSPIN[0:1] Low to First CCLK Edge Setup Time	2cyc	600+6cyc	ns
f_{MAXSPI}	Max CCLK Frequency	—	20	MHz
t_{SUSPI}	SOSPI Data Setup Time Before CCLK	7	—	ns
t_{HSPI}	SOSPI Data Hold Time After CCLK	10	—	ns
sysCONFIG SPI Port (Slave)				
$f_{MAXSPIS}$	Slave CCLK Frequency	—	25	MHz
t_{RF}	Rise and Fall Time	50	—	mV/ns
t_{STCO}	Falling Edge of CCLK to SOSPI Active	—	20	ns
t_{STOZ}	Falling Edge of CCLK to SOSPI Disable	—	20	ns
t_{STSU}	Data Setup Time (SISPI)	8	—	ns
t_{STH}	Data Hold Time (SISPI)	10	—	ns
t_{STCKH}	CCLK Clock Pulse Width, High	0.02	200	µs
t_{STCKL}	CCLK Clock Pulse Width, Low	0.02	200	µs
t_{STVO}	Falling Edge of CCLK to Valid SOSPI Output	—	20	ns
t_{SCS}	CSSPISN High Time	25	—	ns
t_{SCSS}	CSSPISN Setup Time	25	—	ns
t_{SCSH}	CSSPISN Hold Time	25	—	ns

1. Re-toggling the PROGRAMN pin is not permitted until the INITN pin is high. Avoid consecutive toggling of PROGRAMN.

Flash Download Time (from On-Chip Flash to SRAM)

Over Recommended Operating Conditions

Symbol	Parameter		Min.	Typ.	Max.	Units
$t_{REFRESH}$	PROGRAMN Low-to-High. Transition to Done High.	XP2-5	—	1.8	2.1	ms
		XP2-8	—	1.9	2.3	ms
		XP2-17	—	1.7	2.0	ms
		XP2-30	—	2.0	2.1	ms
		XP2-40	—	2.0	2.3	ms
	Power-up refresh when PROGRAMN is pulled up to V_{CC} (V_{CC}=V_{CC} Min)	XP2-5	—	1.8	2.1	ms
		XP2-8	—	1.9	2.3	ms
		XP2-17	—	1.7	2.0	ms
		XP2-30	—	2.0	2.1	ms
		XP2-40	—	2.0	2.3	ms

Flash Program Time

Over Recommended Operating Conditions

Device	Flash Density		Program Time	Units
			Typ.	
XP2-5	1.2M	TAG	1.0	ms
		Main Array	1.1	s
XP2-8	2.0M	TAG	1.0	ms
		Main Array	1.4	s
XP2-17	3.6M	TAG	1.0	ms
		Main Array	1.8	s
XP2-30	6.0M	TAG	2.0	ms
		Main Array	3.0	s
XP2-40	8.0M	TAG	2.0	ms
		Main Array	4.0	s

Flash Erase Time

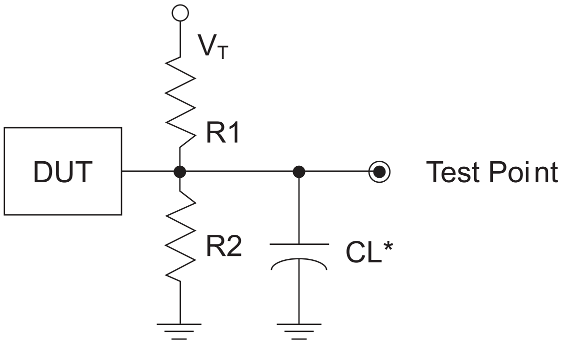
Over Recommended Operating Conditions

Device	Flash Density		Erase Time	Units
			Typ.	
XP2-5	1.2M	TAG	1.0	s
		Main Array	3.0	s
XP2-8	2.0M	TAG	1.0	s
		Main Array	4.0	s
XP2-17	3.6M	TAG	1.0	s
		Main Array	5.0	s
XP2-30	6.0M	TAG	2.0	s
		Main Array	7.0	s
XP2-40	8.0M	TAG	2.0	s
		Main Array	9.0	s

Switching Test Conditions

Figure 3-11 shows the output test load that is used for AC testing. The specific values for resistance, capacitance, voltage, and other test conditions are shown in Table 3-6.

Figure 3-11. Output Test Load, LVTTL and LVCMOS Standards



*CL Includes Test Fixture and Probe Capacitance

Table 3-6. Test Fixture Required Components, Non-Terminated Interfaces

Test Condition	R_1	R_2	C_L	Timing Ref.	V_T
LVTTL and other LVCMOS settings (L -> H, H -> L)	∞	∞	0pF	LVCMOS 3.3 = 1.5V	—
				LVCMOS 2.5 = $V_{CCIO}/2$	—
				LVCMOS 1.8 = $V_{CCIO}/2$	—
				LVCMOS 1.5 = $V_{CCIO}/2$	—
				LVCMOS 1.2 = $V_{CCIO}/2$	—
LVCMOS 2.5 I/O (Z -> H)	∞	1MΩ		$V_{CCIO}/2$	—
LVCMOS 2.5 I/O (Z -> L)	1MΩ	∞		$V_{CCIO}/2$	V_{CCIO}
LVCMOS 2.5 I/O (H -> Z)	∞	100		V_{OH} - 0.10	—
LVCMOS 2.5 I/O (L -> Z)	100	∞		V_{OL} + 0.10	V_{CCIO}

Note: Output test conditions for all other interfaces are determined by the respective standards.

PICs and DDR Data (DQ) Pins Associated with the DDR Strobe (DQS) Pin

PICs Associated with DQS Strobe	PIO Within PIC	DDR Strobe (DQS) and Data (DQ) Pins
For Left and Right Edges of the Device		
P[Edge] [n-4]	A	DQ
	B	DQ
P[Edge] [n-3]	A	DQ
	B	DQ
P[Edge] [n-2]	A	DQ
	B	DQ
P[Edge] [n-1]	A	DQ
	B	DQ
P[Edge] [n]	A	[Edge]DQSn
	B	DQ
P[Edge] [n+1]	A	DQ
	B	DQ
P[Edge] [n+2]	A	DQ
	B	DQ
P[Edge] [n+3]	A	DQ
	B	DQ
For Top and Bottom Edges of the Device		
P[Edge] [n-4]	A	DQ
	B	DQ
P[Edge] [n-3]	A	DQ
	B	DQ
P[Edge] [n-2]	A	DQ
	B	DQ
P[Edge] [n-1]	A	DQ
	B	DQ
P[Edge] [n]	A	[Edge]DQSn
	B	DQ
P[Edge] [n+1]	A	DQ
	B	DQ
P[Edge] [n+2]	A	DQ
	B	DQ
P[Edge] [n+3]	A	DQ
	B	DQ
P[Edge] [n+4]	A	DQ
	B	DQ

Notes:

1. “n” is a row PIC number.
2. The DDR interface is designed for memories that support one DQS strobe up to 16 bits of data for the left and right edges and up to 18 bits of data for the top and bottom edges. In some packages, all the potential DDR data (DQ) pins may not be available. PIC numbering definitions are provided in the “Signal Names” column of the Signal Descriptions table.